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August 2018

ISL9R860P2, ISL9R860S3ST 8 A, 600 V, STEALTH™ Diode

Features

- Stealth Recovery trr = 28 ns (@ IF = 8 A)
- Max Forward Voltage, VF = 2.4 V (@ TC = 25°C)
- 600 V Reverse Voltage and High Reliability
- · Avalanche Energy Rated
- RoHS Compliant

Applications

- SMPS FWD
- · Hard Switched PFC Boost Diode
- · UPS Free Wheeling Diode
- Motor Drive FWD
- · Snubber Diode

Description

The ISL9R860P2, ISL9R860S3ST is a STEALTH™ diode optimized for low loss performance in high frequency hard switched applications. The STEALTH™ family exhibits low reverse recovery current (I_{RR}) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low I_{RR} and short ta phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH™ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Package JEDEC TO-220AC-2L JEDEC TO-263AB(D²-PAK) CATHODE (FLANGE) N/C ANODE N/C ANODE

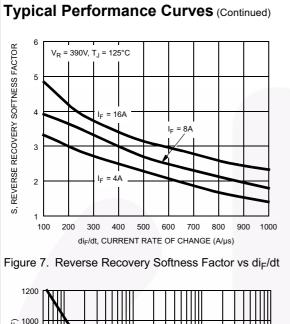
Device Maximum Ratings Tc= 25°C unless otherwise noted

Symbol	Parameter	Ratings	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current (T _C = 147°C)	8	Α
I _{FRM}	Repetitive Peak Surge Current (20kHz Square Wave)	16	Α
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)	100	Α
P _D	Power Dissipation	85	W
E _{AVL}	Avalanche Energy (1 A, 40 mH)	20	mJ
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to 175	°C
T _L T _{PKG}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10s Package Body for 10s, See Techbrief TB334	300 260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

ait ituii	nber To	p Mark	Package		Packing Me	ethod	Reel Size	Тар	e Wic	ith (Quantity
ISL9R860F	P2 R	860P2	TO-220AC-2L		Tube N/A		N/A			50	
ISL9R860S3ST R860S3S TO		TO-263AB(D ² -	-PAK)	Reel		13" Dia		24mm		800	
Electri	cal Cha	racteri	Stics T _C = 25	5°C ur	nless otherwise	noted		•		•	
Symbol				Test Conditions		Min	n Typ Ma		ax Unit		
Off State	- Charac	teristics					<u> </u>			•	
I _R		Instantaneous Reverse Current		ī	V _R = 600 V	Tc=	: 25°C		-	100	μА
							: 125°C	-	-	1.0	mA
On State	Charac	taristics					<u> </u>			ı	
V _F				1	I _F = 8 A	Т. =	25°C	_	2.0	2.4	T V
٧,	Instantaneous Forward Voltage		ara voltage	"	1F - 0 A	To =	: 125°C		1.6	2.0	T V
	01					1.0	.200				<u> </u>
	Charac			1					1 00	1	
CJ	Junction (Capacitano	е		$V_R = 10 \text{ V}, I_F = 0$	Α		-	30	-	pF
Switchir	ng Chara	cteristic	s								
t _{rr}	Reverse I	Reverse Recovery Time			$I_F = 1 A, di_F/dt =$	100 Α/μ	s, V _R = 30 V	-	18	25	ns
					$I_F = 8 A, di_F/dt =$	100 A/u:	s, V _R = 30 V	_	21	30	ns
4		Reverse Recovery Time			1 , , , , , , , ,						
t _{rr}	Reverse I	Recovery T	īme		I _F = 8 A,		, K	-	28	-	ns
I _{rr}		Recovery T Recovery C			I _F = 8 A, di _F /dt = 200 A/μs	5,					ns A
I _{rr}	Reverse I		Current		I _F = 8 A,	5,	-	-	28	-	
	Reverse F	Recovery C	Current Charge		I _F = 8 A, di _F /dt = 200 A/μs	5,	, IV	-	28 3.2	-	Α
I _{rr}	Reverse F Reverse F	Recovery C	Current Charge Time		$I_F = 8 A,$ $di_F/dt = 200 A/\mu s$ $V_R = 390 V, T_C =$ $I_F = 8 A,$ $di_F/dt = 200 A/\mu s$	s, = 25°C		-	28 3.2 50	- - -	A nC
I _{rr} Q _{rr} t _{rr}	Reverse I Reverse I Reverse I Softness	Recovery C Recovery C Recovery T	Current Charge Time		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C =$ $I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$	s, = 25°C		-	28 3.2 50 77		A nC
I _{rr} Q _{rr}	Reverse I Reverse I Reverse I Softness	Recovery C Recovery C Recovery T Factor (t _b /t	Current Charge Time a) Current		$I_F = 8 A,$ $di_F/dt = 200 A/\mu s$ $V_R = 390 V, T_C =$ $I_F = 8 A,$ $di_F/dt = 200 A/\mu s$	s, = 25°C		-	28 3.2 50 77 3.7	- - -	A nC ns
Irr Qrr trr S Irr Qrr	Reverse I Reverse I Reverse I Softness Reverse I	Recovery C Recovery C Recovery T Factor (t _b /t Recovery C	Current Charge Time a) Current Charge		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C =$ $I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$	s, = 25°C		-	28 3.2 50 77 3.7 3.4	- - - -	A nC ns
I _{rr} Q _{rr}	Reverse I Reverse I Reverse I Softness Reverse I Reverse I	Recovery C Recovery C Recovery T Factor (t _b /t Recovery C Recovery C	Current Charge Time a) Current Charge Time		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C = I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$ $T_C = 125^{\circ}\text{C}$ $I_F = 8 \text{ A},$ $di_F/dt = 600 \text{ A}/\mu\text{s}$	s, = 25°C			28 3.2 50 77 3.7 3.4 150	- - - - -	A nC ns A nC
I _{rr} Q _{rr}	Reverse I Reverse I Softness Reverse I Reverse I Reverse I Softness	Recovery C Recovery C Recovery T Factor (t _b /t Recovery C Recovery C Recovery T	Current Charge Time a) Current Charge Time Charge Time a)		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C = I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$ $T_C = 125^{\circ}\text{C}$ $I_F = 8 \text{ A},$ $di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$	s, = 25°C			28 3.2 50 77 3.7 3.4 150	- - - - -	A nC ns A nC
I _{rr}	Reverse I Reverse I Softness Reverse I Reverse I Reverse I Softness Reverse I	Recovery C Recovery C Recovery T Factor (t _b /t Recovery C Recovery T Factor (t _b /t	Current Charge Time a) Current Charge Time Charge Current Charge Time a) Current		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C = I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$ $T_C = 125^{\circ}\text{C}$ $I_F = 8 \text{ A},$ $di_F/dt = 600 \text{ A}/\mu\text{s}$	s, = 25°C		-	28 3.2 50 77 3.7 3.4 150 53 2.5	- - - - - - -	A nC ns A nC ns
I _{II}	Reverse I Reverse I Softness Reverse I Reverse I Reverse I Softness Reverse I Reverse I	Recovery C Recovery T Recovery T Factor (t _b /t Recovery C Recovery T Factor (t _b /t Recovery C	Current Charge Time a) Current Charge Time Current Charge Current Charge Current Charge		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C = I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$ $T_C = 125^{\circ}\text{C}$ $I_F = 8 \text{ A},$ $di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$	s, = 25°C		-	28 3.2 50 77 3.7 3.4 150 53 2.5 6.5	- - - - - - - - -	A nC ns A nC ns
I _{rr}	Reverse I Reverse I Softness Reverse I Reverse I Reverse I Reverse I Reverse I Reverse I Maximum	Recovery C Recovery T Recovery T Factor (t _b /t Recovery C Recovery T Factor (t _b /t Recovery C Recovery C Recovery C	Current Charge Time a) Current Charge Time Current Charge Current Charge Current Charge		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C = I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$ $T_C = 125^{\circ}\text{C}$ $I_F = 8 \text{ A},$ $di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$	s, = 25°C			28 3.2 50 77 3.7 3.4 150 53 2.5 6.5 195	- - - - - - - - - -	A nC ns A nC ns
$ \begin{array}{c c} I_{rr} \\ \hline Q_{rr} \\ \hline t_{rr} \\ \hline S \\ \hline I_{rr} \\ \hline Q_{rr} \\ \hline t_{rr} \\ \hline S \\ \hline I_{rr} \\ \hline Q_{rr} \\ \hline dI_{M}/dt \\ \hline \end{array} $	Reverse I Reverse I Softness Reverse I Reverse I Reverse I Softness Reverse I Maximum	Recovery C Recovery T Recovery T Factor (t _b /t Recovery C Recovery T Factor (t _b /t Recovery C Recovery C Recovery C di/dt durin	Current Charge Time a) Current Charge Time Charge Current Charge Gurrent Charge g t _b		$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C = I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$ $T_C = 125^{\circ}\text{C}$ $I_F = 8 \text{ A},$ $di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$	s, = 25°C			28 3.2 50 77 3.7 3.4 150 53 2.5 6.5 195	- - - - - - - - - -	A nC ns A nC ns A nC A/µs
I _{rr}	Reverse I Reverse I Softness Reverse I Reverse I Reverse I Reverse I Reverse I Maximum Charact	Recovery C Recovery T Factor (t _b /t Recovery C Recovery C Recovery T Factor (t _b /t Recovery C Recovery C di/dt durin	Current Charge Time a) Current Charge Time Current Charge Current Charge Current Charge	se	$I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V}, T_C = I_F = 8 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$ $T_C = 125^{\circ}\text{C}$ $I_F = 8 \text{ A},$ $di_F/dt = 600 \text{ A}/\mu\text{s}$ $V_R = 390 \text{ V},$	s, = 25°C			28 3.2 50 77 3.7 3.4 150 53 2.5 6.5 195	- - - - - - - - - -	A nC ns A nC ns

Typical Performance Curves 175°C 150°C REVERSE CURRENT (µA) FORWARD CURRENT (A) 12 10 125°C 8 100°C 100°C 6 2 0.5 0.75 1.25 1.5 1.75 V_F, FORWARD VOLTAGE (V) V_R, REVERSE VOLTAGE (V) Figure 1. Forward Current vs Forward Voltage Figure 2. Reverse Current vs Reverse Voltage V_R = 390V, T_J = 125°C V_R = 390V, T_J = 125°C t_b AT $d_F/dt = 200A/\mu s$, $500A/\mu s$, $800A/\mu s$ 60 t, RECOVERY TIMES (ns) t, RECOVERY TIMES (ns) 60 50 40 30 30 20 10 10 t_a AT $di_F/dt = 200A/\mu s$, $500A/\mu s$, $800A/\mu s$ 300 400 500 600 700 800 900 1000 di_F/dt, CURRENT RATE OF CHANGE (A/µs) 100 I_F, FORWARD CURRENT (A) Figure 4. t_a and t_b Curves vs di_F/dt Figure 3. t_a and t_b Curves vs Forward Current V_R = 390V, T_J = 125°C $V_R = 390V, T_J = 125^{\circ}C$ $di_F/dt = 800A/\mu s$ € MAX REVERSE RECOVERY CURRENT (A) 10 MAX REVERSE RECOVERY CURRENT 12 9 10 8 $di_F/dt = 500A/\mu s$ 7 6 6 5 $di_F/dt = 200A/\mu s$ 0 16 I_F, FORWARD CURRENT (A) di_F/dt, CURRENT RATE OF CHANGE (A/μs) Figure 5. Maximum Reverse Recovery Current Figure 6. Maximum Reverse Recovery Current vs Forward Current vs di_F/dt



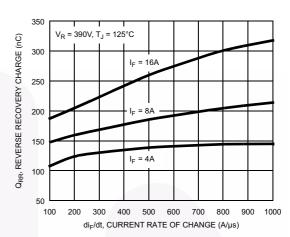


Figure 8. Reverse Recovery Charge vs di_F/dt

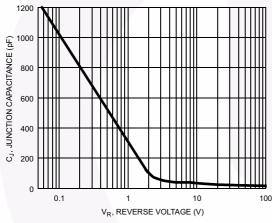


Figure 9. Junction Capacitance vs Reverse Voltage

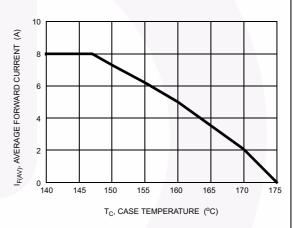


Figure 10. DC Current Derating Curve

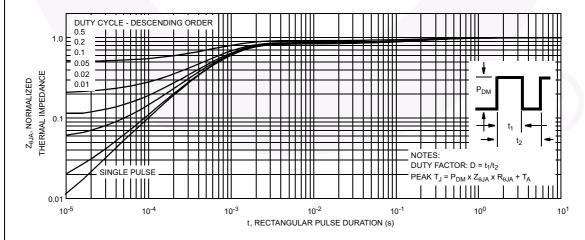
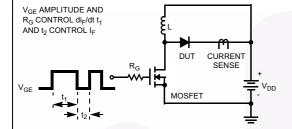


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuits and Waveforms



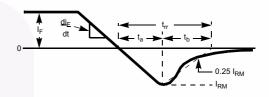
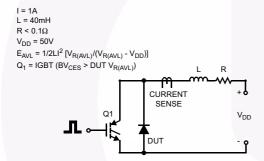


Figure 12. t_{rr} Test Circuit

Figure 13. t_{rr} Waveforms and Definitions



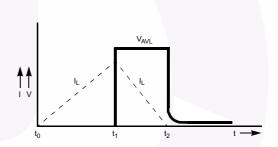


Figure 14. Avalanche Energy Test Circuit

Figure 15. Avalanche Current and Voltage Waveforms

Mechanical Dimensions

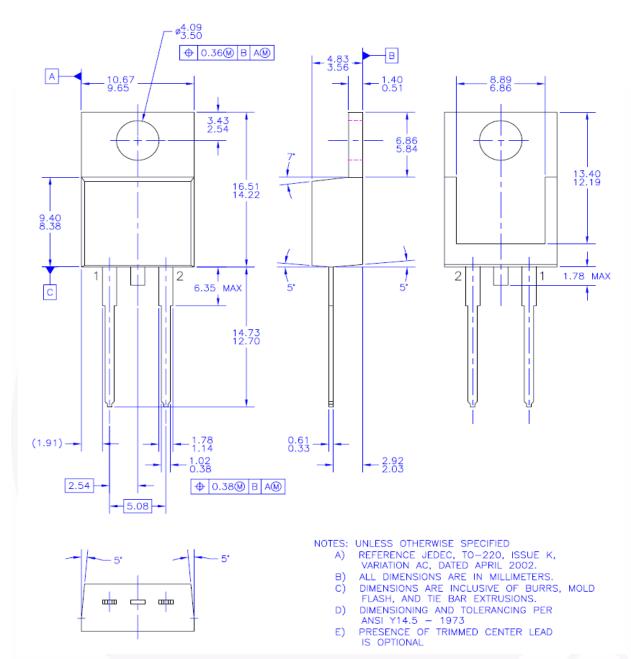


Figure 16. TO-220 2L - 2LD, TO220, JEDEC TO-220 VARIATION AC

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9.45 10.00 (6.40)1.78 MAX 3.80 (2.12)5.08 LAND PATTERN RECOMMENDATION UNLESS NOTED, ALL DIMS TYPICAL 5,08 → 0.25 M B AM 6.22 MIN 6.86 MIN 15.88 14.61 SEE DETA|L A NOTES: UNLESS OTHERWISE SPECIFIED A) ALL DIMENSIONS ARE IN MILLIMETERS. B) REFERENCE JEDEC, TO-263, VARIATION AB. C) DIMENSIONING AND TOLERANCING PER ANSI Y14,5M - 1994. D) LOCATION OF THE PIN HOLE MAY VARY GAGE PLANE (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE). E) LANDPATTERN RECOMMENDATION PER IPC 0.25 TO254P1524X482-3N F) FILENAME: TO263A02REV6 O.10 B 0.25 MAX (5.38) DETAIL A, ROTATED 90°

Figure 17. TO-263 2L (D2PAK) - 2LD,TO263, SURFACE MOUNT

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Package Dimensions





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